

PATENT 8733.055.00

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Youn Gyoung CHANG et al.

Group Art Unit: 2815

4-11-01

Application No.: 09/466,961

Examiner: Paul E. Brock III. Thouse

Filed: December 20, 1999

For: THIN FILM TRANSISTOR TYPE OPTICAL DETECTING SENSOR

## **AMENDMENT**

Commissioner of Patents Washington, D.C. 20231

Sir:

In response to the Examiner's Office Action mailed on May 31, 2001, the following amendments and remarks are respectfully submitted.

## IN THE DRAWINGS

Please enter the legend -- Related Art-- to Figures 1, 2, and 3.

Change the designation "29" to --21-- in Figure 2.

## IN THE SPECIFICATION

On page 7, Paragraph beginning at Line 6, please amend as follows (Exhibit I is a marked up version of the amended Specification paragraph):

As shown in Fig. 4b, a first insulating layer 117, which is preferably one of the group consisting of aluminum oxide (Al<sub>2</sub>O<sub>x</sub>), silicon oxide (SiO<sub>x</sub>) and tantalum oxide (TaO<sub>x</sub>), is deposited on the substrate 110 while covering the switch gate 115, the first capacitor electrode 113 and the sensor gate 111. An amorphous silicon layer and an n+ amorphous layer are

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